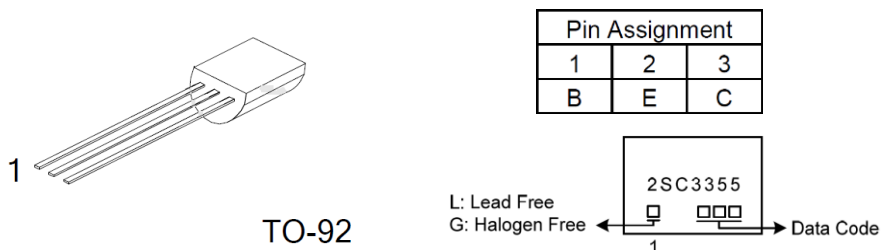


Image serves as a representation only.

ABSTRACT

The 2SC3355 is a silicon epitaxial transistor in NPN configuration. This high frequency, low noise amplifier boasts a high power gain. The transistor is encased in a compact three pin durable plastic TO-92 package.



ABSOLUTE MAXIMUM RATING (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-base voltage	V _{CB0}	20	V
Collector-emitter voltage	V _{CEO}	12	V
Emitter-base voltage	V _{EBO}	3	V
Collector current	I _C	100	mA
Total power dissipation	P _T	600	mW
Junction Temperature	T _J	125	°C
Operating Temperature	T _{OPR}	-20 ~ +85	°C
Storage Temperature	T _{STG}	-40 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cutoff Current	I _{CB0}	V _{CB} =10V, I _E =0			1.0	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =1V, I _C =0			1.0	μA
DC Current Gain	h _{FE}	V _{CE} =10V, I _C =20mA	50		300	
Gain bandwidth Product	f _T	V _{CE} =10V, I _C =20mA		7		GHz
Feed-Back Capacitance	C _{re}	V _{CB} =10V, I _E =0, f=1.0MHz			1.0	pF
Noise Figure	NF	V _{CE} =10V, I _C =7mA, f=1.0GHz		1.1		dB